描述 / Descriptions

N 沟道 TO-263 塑封封装场效应管。

N-CHANNEL MOSFET in a TO-263 Plastic Package.

特征 / Features

$R_{DS(on)}$小，栅极电荷低，快速开关特性，无卤产品。

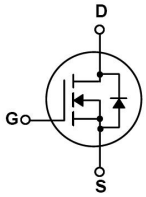
Low $R_{DS(on)}$,Low Gate Charge, Fast Switching,Halogen-free Product.

用途 / Applications

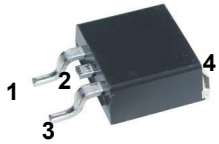
用于 AC-DC 开关电源，DC-DC 电源转换器，高压 H 桥 PWM 马达驱动。

Suited for AD-DC Power switch,DC-DC Power converter,High Voltage H-Bridge PWM Motor Drive.

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning



PIN1：G　　PIN 2、4：D　　PIN 3：S

放大及印章代码 / h_{FE} Classifications & Marking

见印章说明。See Marking Instructions.

极限参数 / Absolute Maximum Ratings(Ta=25℃)

参数 Parameter		符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage		V_{DSS}	70	V
Drain Current[G]		I_D(Tc=25℃)	80	A
		I_D(Tc=100℃)	62	A
Drain Current - Pulsed[C]		I_{DM}	308	A
Gate-Source Voltage		V_{GS}	±20	V
Single Pulsed Avalanche Energy(L=0.5mH)		E_{AS}	350	mJ
Avalanche Current		I_{AS}	30	A
Power Dissipation[B]		P_D(Tc=25℃)	175	W
		P_D(Tc=100℃)	67	W
Operating and Storage Temperature Range		T_J,T_{STG}	-55 to 150	℃
Maximum Junction-to-Ambient[A]	Steady-State	$R_{\theta JA}$	62	℃/W
Maximum Junction-to-Case[B]	Steady-State	$R_{\theta JC}$	0.7	℃/W

电性能参数 / Electrical Characteristics(Ta=25℃)

参数 Parameter	符号 Symbol	测试条件 Test Conditions		最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V	I_D=250μA	70			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=70V	V_{GS}=0V			1	μA
		V_{DS}=70V	T_J=55℃			5	
Gate-Body Leakage Current Forward	I_{GSS}	V_{GS}=±20V	V_{DS}=0V			100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}	I_D=250μA	2.0	2.8	4.0	V
Total gate charge	$R_{DS(on)}$	V_{GS}=10V	I_D=35A		5.8	7	mΩ
Drain-Source Diode Forward Voltage	V_{SD}	V_{GS}=0V	I_S=1A			1.4	V

电性能参数 / Electrical Characteristics(Ta=25℃)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Gate resistance	R_g	V_{GS}=0V V_{DS}=0V f=1MHz		1.25		Ω
Input Capacitance	C_{iss}	V_{DS}=30V V_{GS}=0V f=1.0MHz		2180		pF
Output Capacitance	C_{oss}			614		pF
Reverse Transfer Capacitance	C_{rss}			110		pF
Total Gate Charge(10V)	Q_g	V_{GS}=10V V_{DS}=30V I_D=20A		53	75	nC
Total Gate Charge(4.5V)	Q_g			22	31	nC
Gate Source Charge	Q_{gs}			17	31	nC
Gate Drain Charge	Q_{gd}			5		nC
Turn-On Delay Time	$t_{d(on)}$	V_{GS}=10V V_{DS}=30V R_L=1.5Ω R_{GEN}=3Ω		18		ns
Turn-On Rise Time	t_r			20		ns
Turn-Off Delay Time	$t_{d(off)}$			33		ns
Turn-Off Fall Time	t_f			4		ns
Body Diode Reverse Recovery Time	t_{rr}	I_F=20A dI/dt=500A/μs		26		ns
Body Diode Reverse Recovery Charge	Q_{rr}	I_F=20A dI/dt=500A/μs		125		nC

A: The value of $R_{\theta JA}$ is measured with the device in a still air environment with T_A =25°C.

B. The power dissipation PD is based on TJ(MAX)=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C: Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C.

D. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to case $R_{\theta JC}$ and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5%max.

F. These curves are based on the junction-to-case thermal impedence which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150°C.

G. The maximum current rating is limited by bond-wires.

电参数曲线图 / Electrical Characteristic Curve

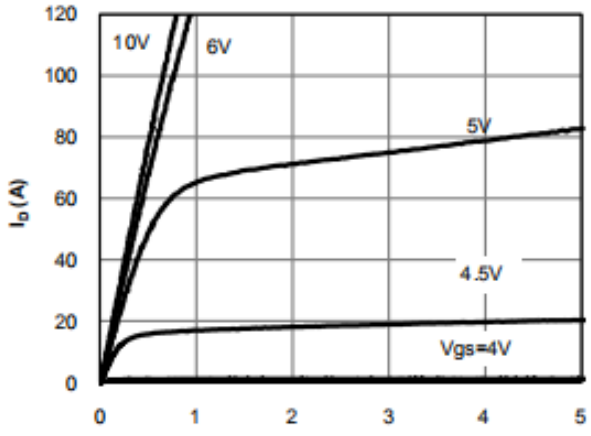


Fig 1: On-Region Characteristics

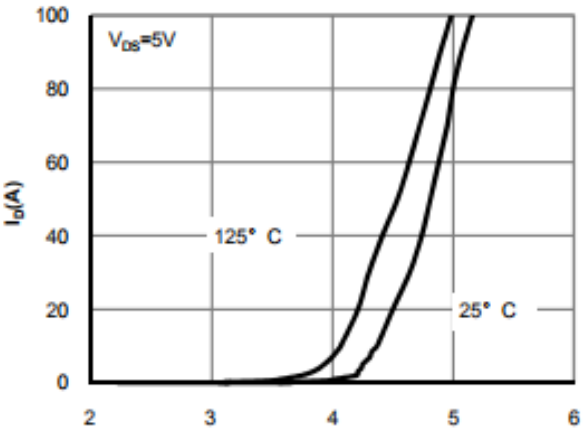


Figure 2: Transfer Characteristics

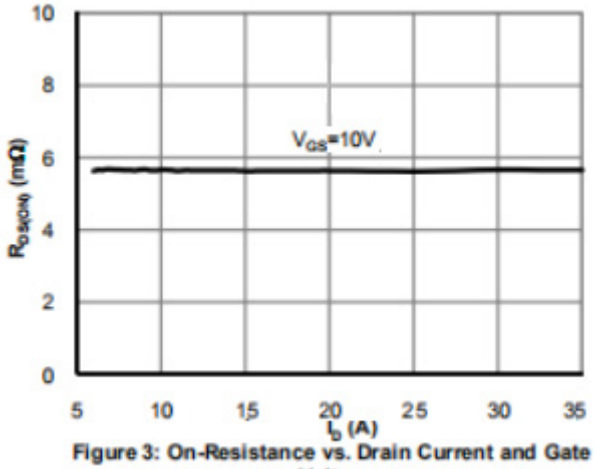


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

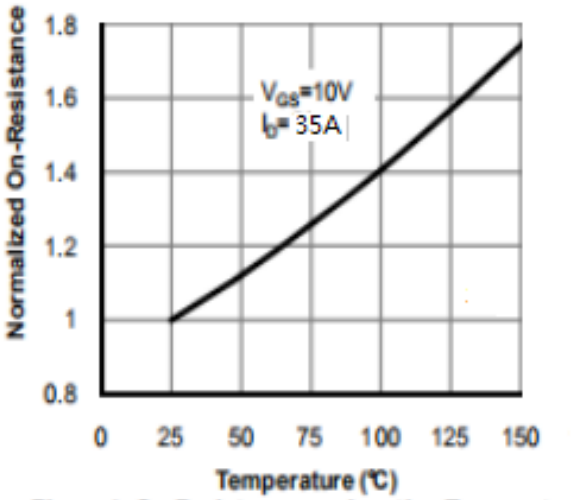


Figure 4: On-Resistance vs. Junction Temperature

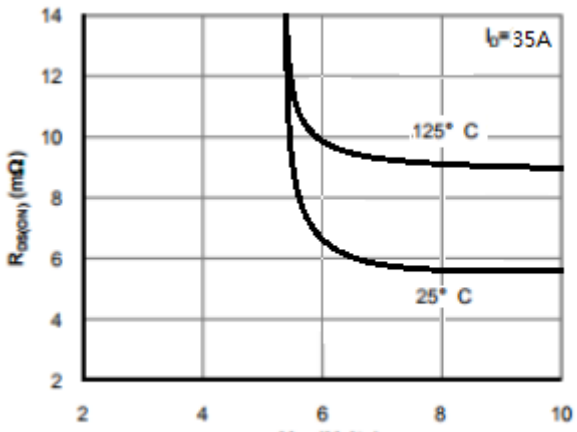


Figure 5: On-Resistance vs. Gate-Source Voltage

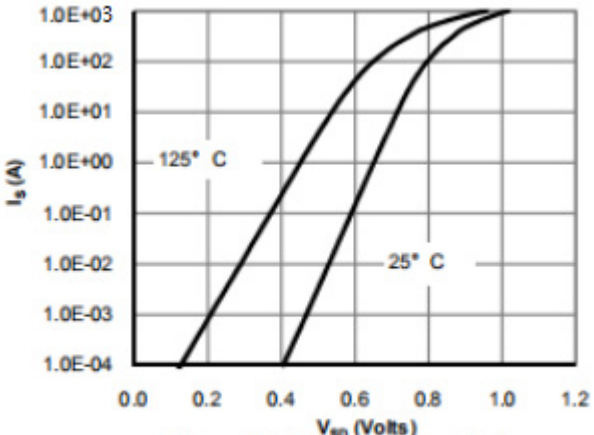


Figure 6: Body-Diode Characteristics

Figure 5: On-Resistance vs. Gate-Source Voltage

电参数曲线图 / Electrical Characteristic Curve

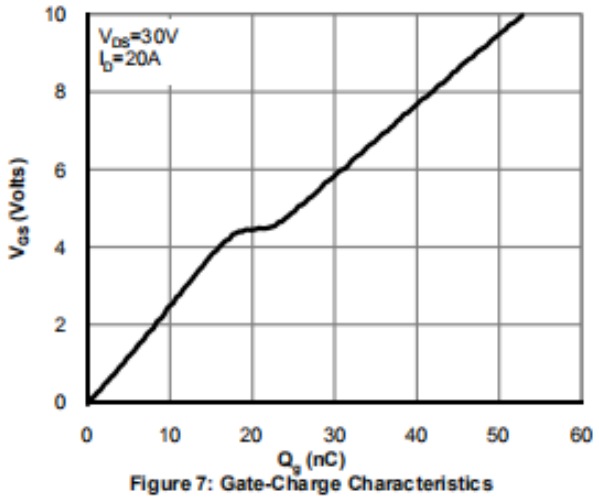


Figure 7: Gate-Charge Characteristics

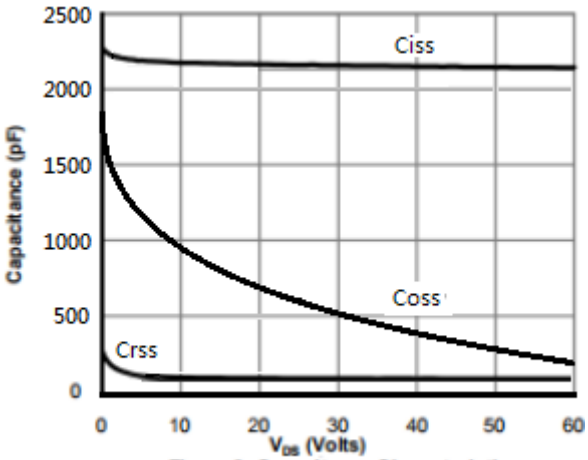


Figure 8: Capacitance Characteristics

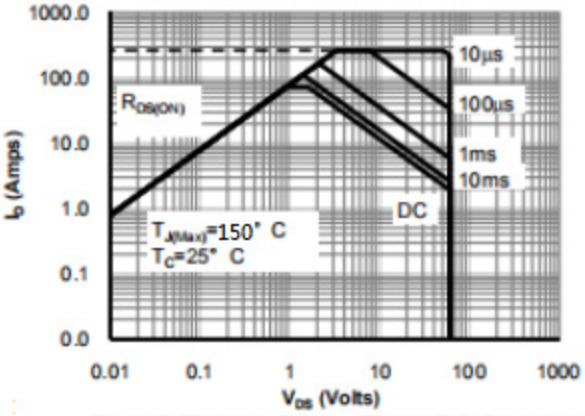


Figure 9: Maximum Forward Biased Safe Operating Area

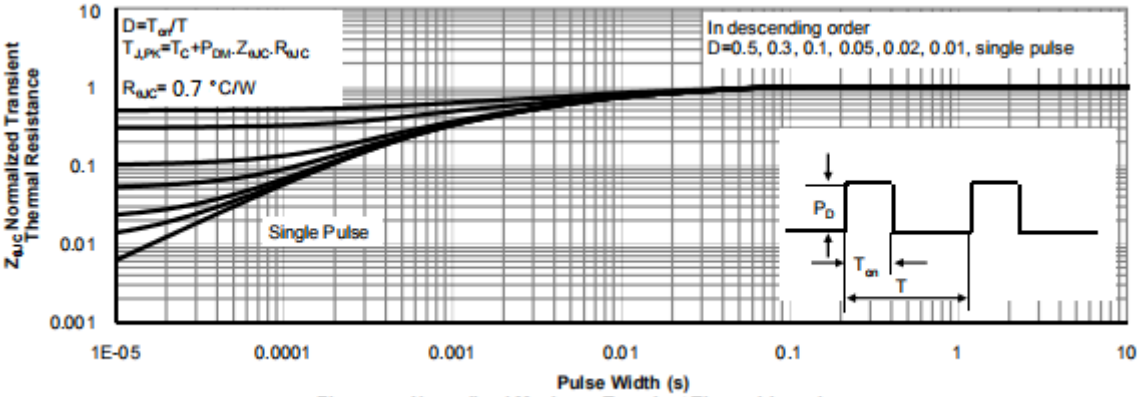
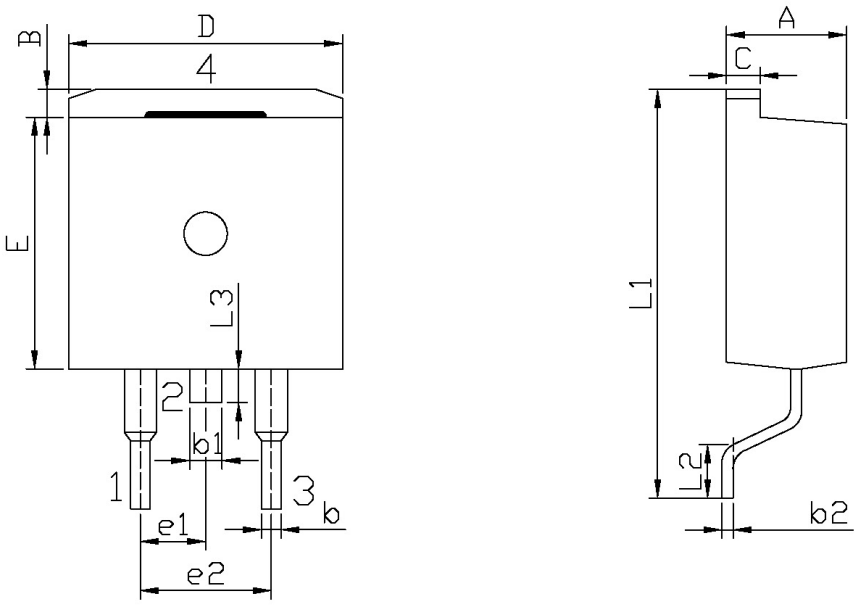


Figure 10: Normalized Maximum Transient Thermal Impedance

外形尺寸图 / Package Dimensions

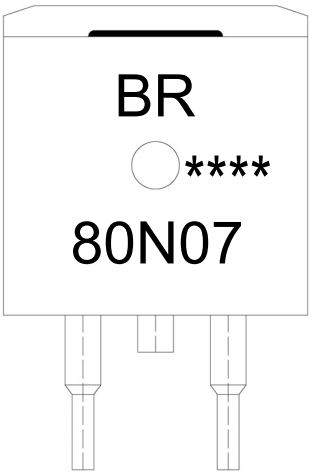


单位：mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	4.30	4.70	E	9.00	9.40
B	1.00	1.40	e1	2.34	2.74
b	0.70	0.90	e2	4.88	5.28
b1	1.15	1.35	L1	15.00	16.00
b2	0.40	0.60	L2	2.24	2.84
C	1.20	1.40	L3	1.20	1.60
D	9.80	10.20			

TO-263

印章说明 / Marking Instructions



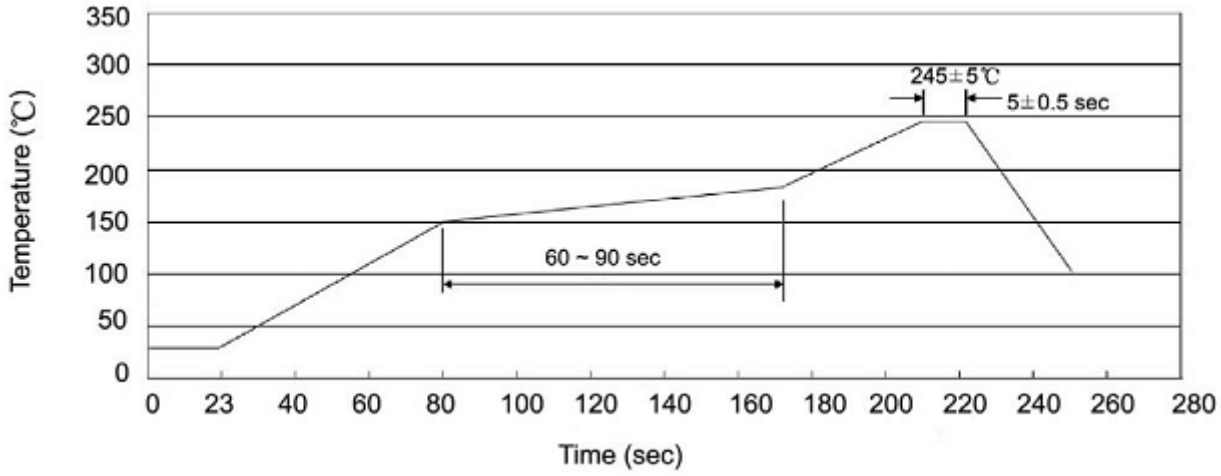
说明：

BR：	为公司代码
80N07：	为型号代码
****：	为生产批号代码，随生产批号变化。

Note:

BR:	Company Code
80N07:	Product Type.
****:	Lot No. Code, code change with Lot No.

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明：

1、预热温度 25～150℃，时间 60～90sec;

2、峰值温度 245±5℃，时间持续为 5±0.5sec;

3、焊接制程冷却速度为 2～10℃/sec.

Note:

1.Preheating:25~150℃, Time:60~90sec.

2.Peak Temp.:245±5℃, Duration:5±0.5sec.

3. Cooling Speed: 2~10℃/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5℃　　时间：10±1 sec.　　Temp.:260±5℃　　Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
TO-263	800	1	800	5	4,000	13″ ×24	360×360×50	385×257×392

套管包装 / TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-263	50	20	1,000	5	5,000	532×33×7.0	555×164×50	575×290×180

使用说明 / Notices